

N-Channel Enhancement Mode Power MOSFET

<p>Description</p> <p>The G2K3N10H uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.</p> <p>General Features</p> <ul style="list-style-type: none"> ● V_{DS} 100V ● I_D (at $V_{GS} = 10V$) 2A ● $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 220mΩ ● $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 230mΩ ● 100% Avalanche Tested ● RoHS Compliant <p>Application</p> <ul style="list-style-type: none"> ● Power switch ● DC/DC converters 	 <p>Schematic diagram</p> <p>SOT-223</p>
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Ordering Information			
Device	Package	Marking	Packaging
G2K3N10H	SOT-223	G2K3N10	2500psc/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Continuous Drain Current	I_D	2	A
Pulsed Drain Current (note1)	I_{DM}	8	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	2.4	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	52	$^\circ\text{C/W}$

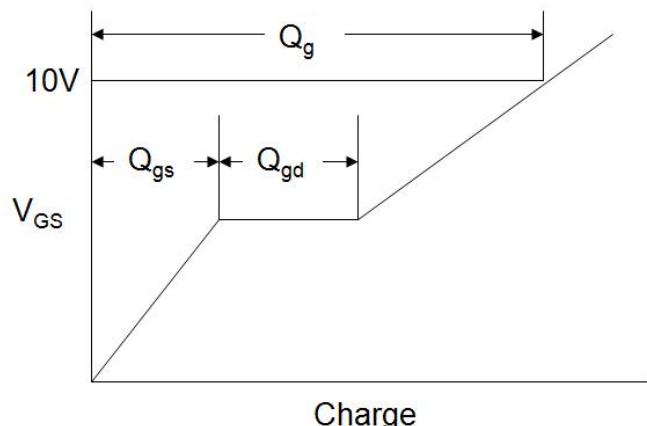
Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 100\text{V}, V_{\text{GS}} = 0\text{V}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1	1.5	2	V
Drain-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 2\text{A}$	--	190	220	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{V}, I_D = 1\text{A}$	--	195	230	
Forward Transconductance	g_{FS}	$V_{\text{GS}} = 5\text{V}, I_D = 2\text{A}$	--	6	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 50\text{V}, f = 1.0\text{MHz}$	--	434	--	pF
Output Capacitance	C_{oss}		--	11	--	
Reverse Transfer Capacitance	C_{rss}		--	10	--	
Total Gate Charge	Q_g	$V_{\text{DD}} = 50\text{V}, I_D = 2\text{A}, V_{\text{GS}} = 10\text{V}$	--	13	--	nC
Gate-Source Charge	Q_{gs}		--	2.5	--	
Gate-Drain Charge	Q_{gd}		--	1.3	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 50\text{V}, I_D = 2\text{A}, R_G = 2.5\Omega$	--	6	--	ns
Turn-on Rise Time	t_r		--	4	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	18	--	
Turn-off Fall Time	t_f		--	5	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	2	A
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 2\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.2	V
Reverse Recovery Charge	Q_{rr}	$I_F = 2\text{A}, V_{\text{GS}} = 0\text{V}$ $dI/dt = 100\text{A/us}$	--	0.34	--	nC
Reverse Recovery Time	T_{rr}		--	98	--	ns

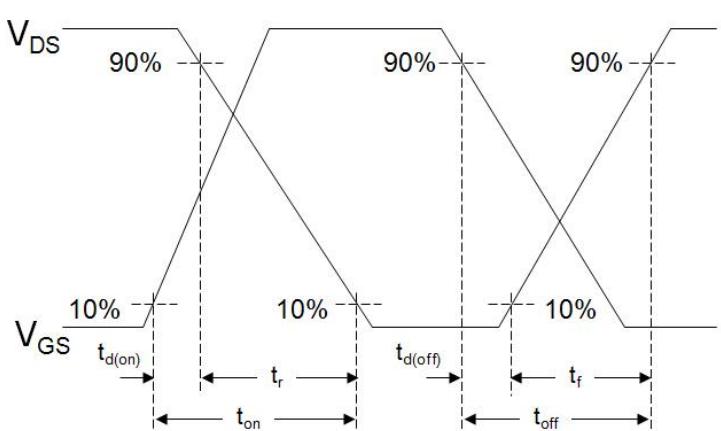
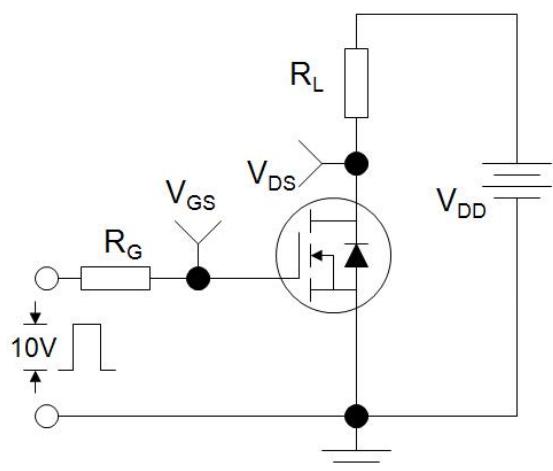
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

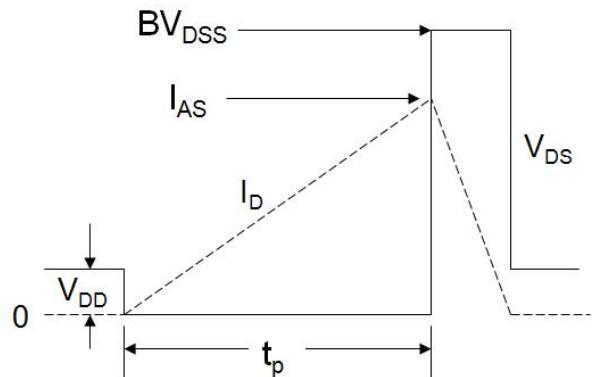
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

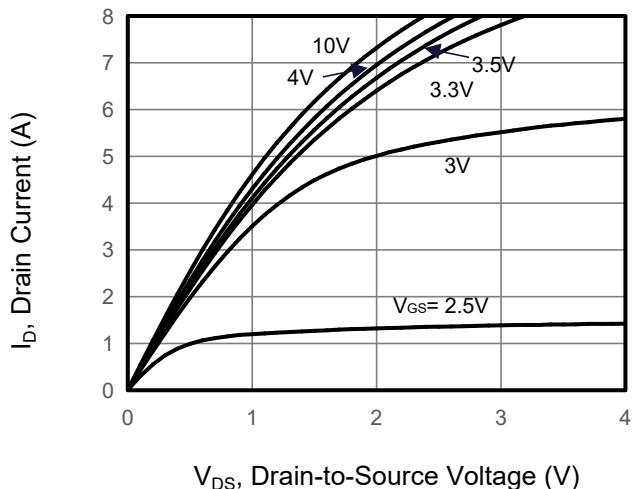


Figure 2. Transfer Characteristics

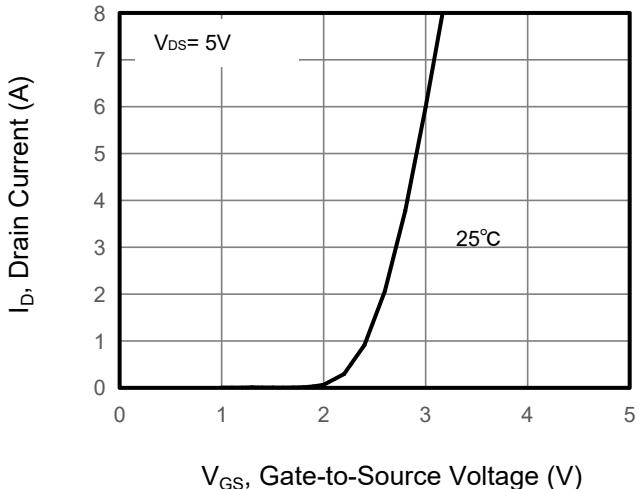


Figure 3. Drain Source On Resistance

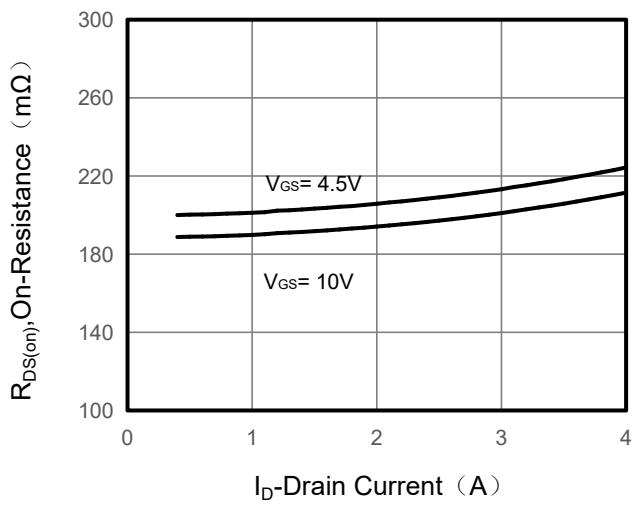


Figure 4. Gate Charge

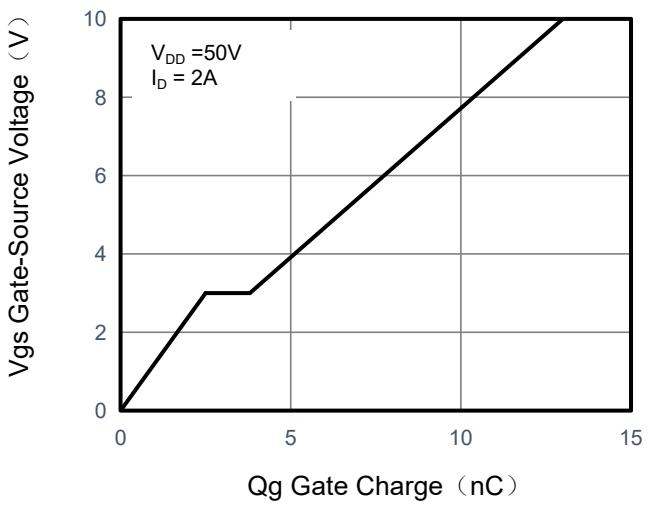


Figure 5. Capacitance

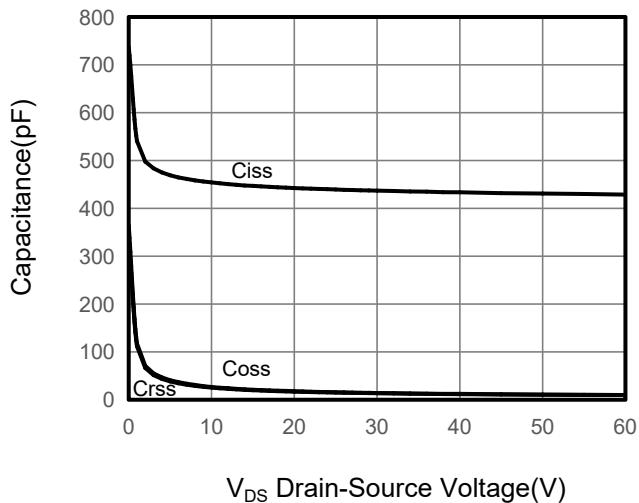
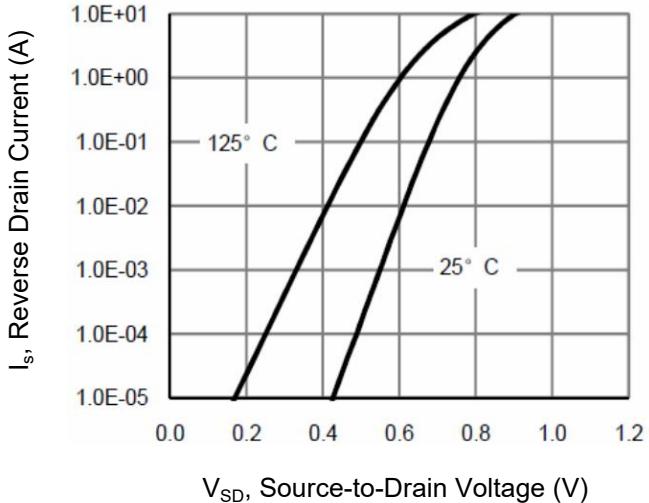


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

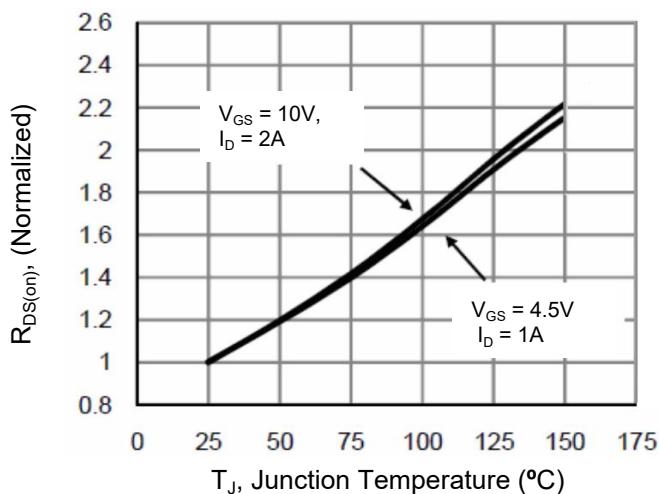


Figure 8. Safe Operation Area

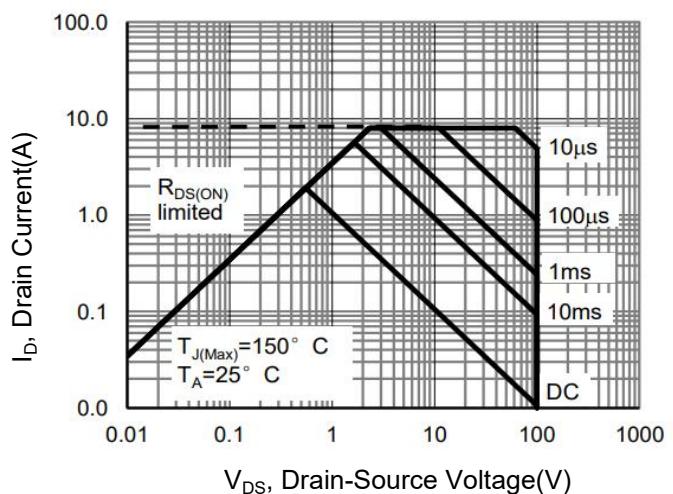
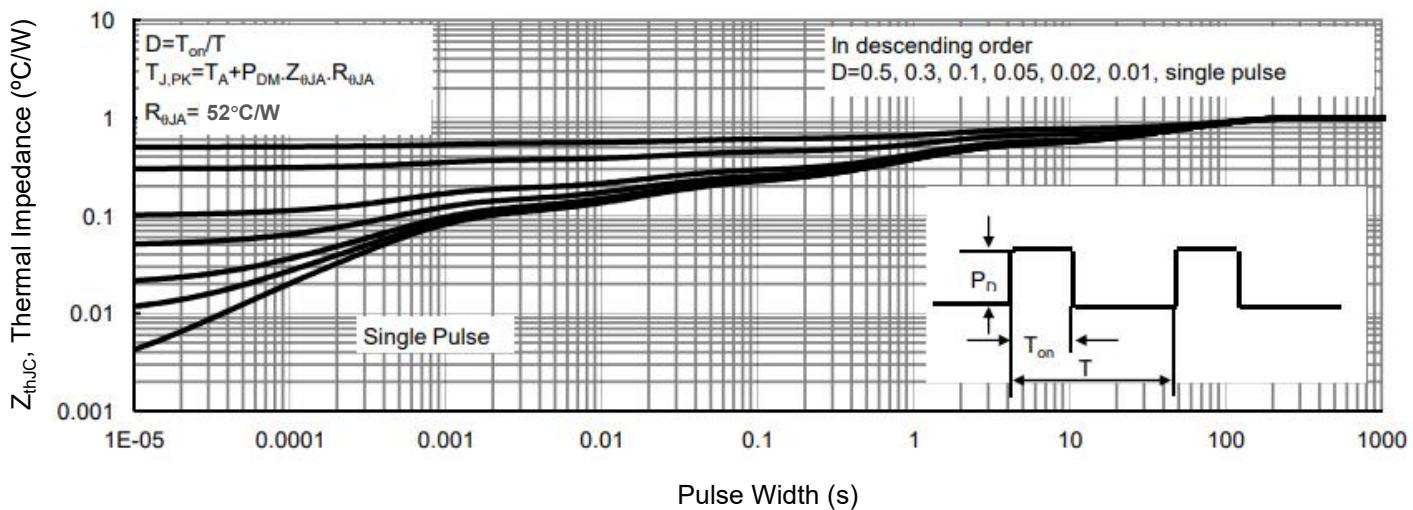
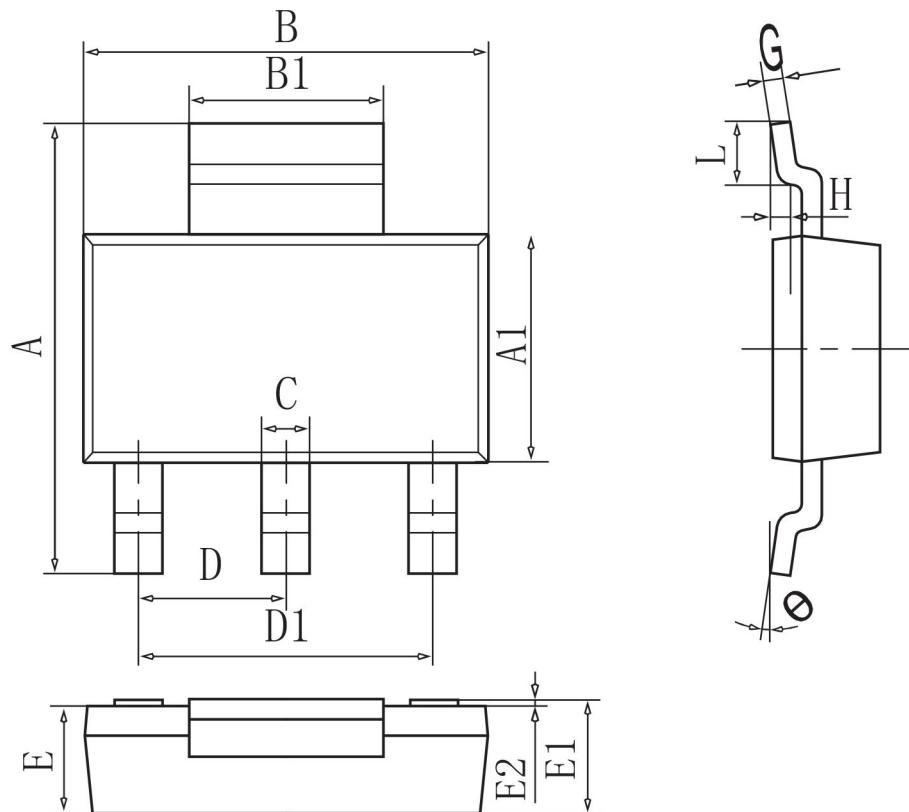


Figure 9. Normalized Maximum Transient Thermal Impedance



SOT-223 Package Information

DIM	MIN	NOM	MAX
A	6.80	7.00	7.20
A1	3.30	3.50	3.70
B	6.40	6.60	6.80
B1	2.96	3.00	3.10
C	0.66	0.70	0.80
D	2.25	2.30	2.35
D1	4.60REF		
E	1.50	1.60	1.70
E1	1.65REF		
E2	0.02	0.06	0.10
G	0.255	0.305	0.355
H	0.25GAUGR		
L	0.90	-	-
Θ	0°	-	10°
All Dimensions in mm			